

Photodiode array chip SC142-01P

Description

SC142-01P chip is fabricated using Silicon Bipolar process technology. The chip is designed to be used in MOS-relay. The chip is optimized for side-by-side MOS-relay design. The spectral response range is 0.85-0.92 nm.

New monolith polysilicon structure.

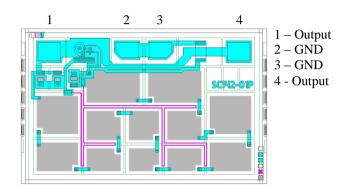
No delamination at high temperatures.

Absolute maximum ratings

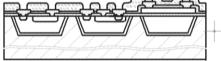
Storage temperature	-65°C to 150°C
Operating junction temperature	-55°C to 125°C

Features

- 12 photodiodes
- Thyristor discharge circuit
- Contact pad's material Aluminium
- Chip size 1.0 x1.6 mm
- Chip thickness 0.32±0.02 mm



Cross section view



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Parameter	Symbol	Unit	Min.	Тур.	Max.	Condition
Open Circuit Voltage	V _{OC}	V	6.0	6.4		1
Short Circuit Current	I _{SC}	μA	3.4	3.8	-	1
Output Voltage	V _{OUT}	V		0.75	1.0	2
Discharge Resistor	R _{DIS}	MOhm	15		50	
Turn-On Time	T _{ON}	ms		0.2		3
Turn-Off Time	T _{OFF}	ms		0.1		

Electrical characteristics ($T = 25 \ ^{\circ}C$)

1 – Parameters are guaranteed when coupled with $IR_{LED} = 10$ mA with peak wavelength $\lambda = 850 \pm 20$ nm, $\Phi_e = 1000 \ \mu\text{W}$ at distance 0.2 mm.

 $2 - No light. I_F = 100 \ \mu A.$

3 – Typical value at IR_{LED} = 10 mA, C_L = 250 pF. The PDA is coupled with LED Φ_e = 500 µW with peak wavelength λ = 850 ±20 nm at distance 0.2 mm.